

Zener Diode Chips for ESD Bidirectional Protection

1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge(ESD) protection application
- 1-2 This specification applies to N/P/N-Type silicon Zener diode chip(Vertical)
Device NO:WT-Z206V-AU4

2. Structure:

- 2-1. Planar type : Silicon Diode.
- 2-2. Electrodes :
Top side : Gold pad(Cathode).
Back side : Gold Layer(Cathode).

3. Size:

- 3-1. *Chip size : 6.88 mils x 6.88 mils (175 μ m x 175 μ m).
 - 3-2. Chip thickness : 3.3 \pm 0.6 mils (85 \pm 15 μ m).
 - 3-3. Bonding pad : 4.5 mils x 4.5 mils (115 μ m x 115 μ m).
 - 3-4. Pattern drawing : Refer to the attached drawing.
- *Including scribing line. The chip size is about 5.9mil(0.150mm) after dicing.

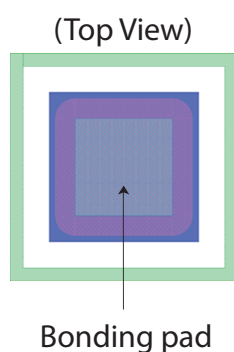
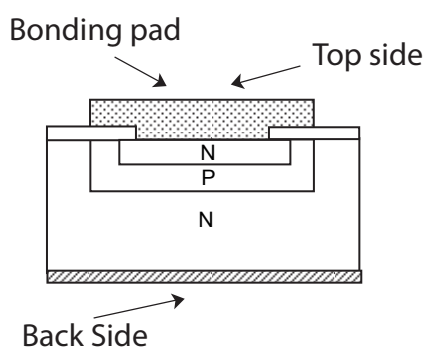
4. Electrical Characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	Vz (Top) Vz (Back)	Iz=5mA	5.3 5.5	- -	6.8 7.0	V
Forward Voltage	Vf	If=20mA	-	-	1.2	v
Leakage Current	IR	V=4V	-	-	100	nA
Electrostatic Discharge	ESD	HBM MIL-STD 883	8.0	-	-	KV

Note:

- 1. Parallel with one LED
- 2. Single pad (one wire bonding applied only)
- 3. Double direction Zener diode protection

5. Drawing:



6. Protection Circuit:

